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JP2004094203 A

CLEANING LIQUID FOR REMOVING
RESIST AND MANUFACTURING
METHOD FOR SEMICONDUCTOR
DEVICE
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[no drawing]

Abstract:

PROBLEM TO BE SOLVED: To provide cleaning liquid for removing resist enhanced in a removing function of resist residual dross and resistance against corrosion of a copper film and an insulator film, when the resist residual dross after etching or ashing, and other etching residual dross are removed in a semiconductor manufacturing process including a copper wiring process, and a manufacturing method for a semiconductor device using the cleaning liquid.
SOLUTION: The cleaning liquid for removing the resist contains salt ((a) component) of hydrofluoric acid and base which does not contain metal, water-soluble organic solvent (b1 component), one or more acid (c component) selected from a group which is composed of organic acid and inorganic acid, and water (d component). Hydrogen ion concentration (pH) of the cleaning liquid is 4 to 8. Moreover, preferably, the cleaning liquid contains additionally ammonium salt (e1 component).

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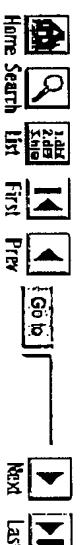
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